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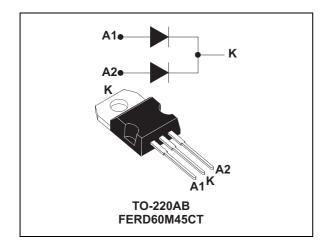




### FERD60M45C

#### Field effect rectifier

**Datasheet - production data** 



### **Description**

This dual rectifier is based on a proprietary technology that achieves the best in class  $V_F/I_R$  for a given silicon surface.

Packaged in TO-220AB this device is intended to be used in switch mode power supplies, or automotive applications

Table 1. Device summary

$I_{F(AV)}$	2 x 30 A
$V_{RRM}$	45 V
V <sub>F</sub> (typ)	0.39 V

#### **Features**

- ST advanced rectifier process
- Stable leakage current over reverse voltage
- · Low forward voltage drop
- High frequency operation

Characteristics FERD60M45C

### 1 Characteristics

Table 2. Absolute ratings (limiting values, per diode at 25° C, unless otherwise stated)

Symbol	Para	Value	Unit		
$V_{RRM}$	Repetitive peak reverse voltage			45	V
I <sub>F(RMS)</sub>	Forward rms current			60	Α
I <sub>F(AV)</sub>	Average forward current, $\delta = 0.5$	T <sub>c</sub> =135° C T <sub>c</sub> =120° C	Per diode Per device	30 60	А
I <sub>FSM</sub>	Surge non repetitive forward current $t_p = 10 \text{ ms sinusoidal}$			275	Α
T <sub>stg</sub>	Storage temperature range			-65 to + 175	°C
T <sub>j</sub>	Maximum operating junction temperature (1)			175	°C

<sup>1.</sup>  $\frac{dPtot}{dTj} < \frac{1}{Rth(j-a)}$  condition to avoid thermal runaway for a diode on its own heatsink

**Table 3. Thermal resistances** 

Symbol	Parameter	Value	Unit	
R <sub>th (j-c)</sub>	Junction to case	Per diode Total	1.6 1.1	°C/W
R <sub>th(c)</sub>	Coupling		0.5	°C/W

When the diodes 1 and 2 are used simultaneously:

 $\Delta T_{j}(\text{diode 1}) = P(\text{diode1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode2}) \times R_{th(c)}.$ 

Table 4. Static electrical characteristics (per diode)

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
I <sub>R</sub> <sup>(1)</sup>	Reverse leakage current	T <sub>j</sub> = 25° C	V - V			550	μΑ
'R`	R Heverse leakage current	T <sub>j</sub> = 125° C	$V_R = V_{RRM}$		25	50	mA
	T <sub>j</sub> = 25° C		0.41	0.45			
V <sub>E</sub> <sup>(2)</sup>	Forward voltage drop	T <sub>j</sub> = 125° C	I <sub>F</sub> = 15 A		0.39	0.425	V
v <sub>F</sub> , ′	Forward voltage drop	T <sub>j</sub> = 25° C			0.51	0.55	V
		T <sub>j</sub> = 125° C	1 IF = 30 A		0.54	0.59	

<sup>1.</sup> Pulse test:  $t_p = 5 \text{ ms}, \delta < 2\%$ 

To evaluate the conduction losses use the following equation:

$$P = 0.39 \times I_{F(AV)} + 0.0067 I_{F}^{2}_{(RMS)}$$

<sup>2.</sup> Pulse test:  $t_p$  = 380  $\mu$ s,  $\delta$  < 2%

FERD60M45C Characteristics

Figure 1. Average forward power dissipation versus average forward current (per diode)

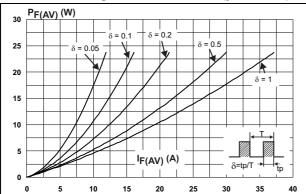


Figure 2. Average forward current versus ambient temperature ( $\delta$  = 0.5, per diode)

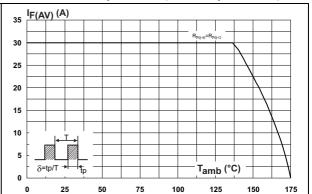
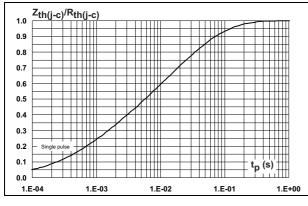


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

Figure 4. Reverse leakage current versus reverse voltage applied (typical values, per diode)



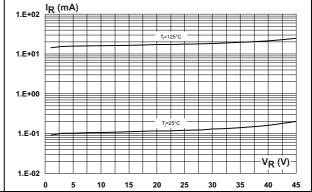
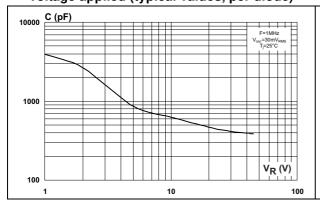
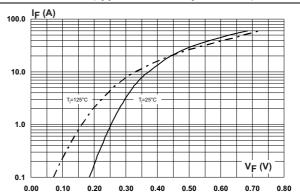


Figure 5. Junction capacitance versus reverse voltage applied (typical values, per diode)

Figure 6. Forward voltage drop versus forward current (typical values, per diode)





Package Information FERD60M45C

### 2 Package Information

- Epoxy meets UL94,V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.4 to 0.6 N⋅m (TO-220AB)

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: <a href="https://www.st.com">www.st.com</a>. ECOPACK<sup>®</sup> is an ST trademark.

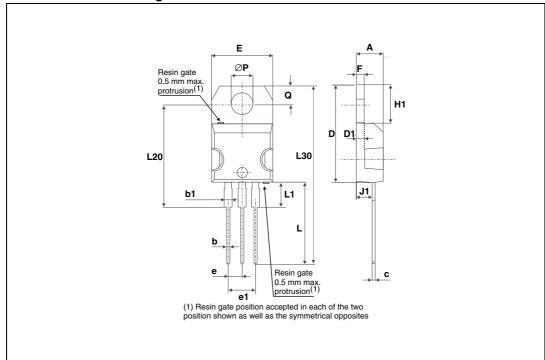


Figure 7. TO-220AB dimension definitions

Table 5. TO-220AB dimension values

	Dimensions				
Ref.	Millimeters		Inc	hes	
	Min.	Max.	Min.	Max.	
А	4.40	4.60	0.17	0.18	
b	0.61	0.88	0.024	0.035	
b1	1.14	1.70	0.045	0.067	
С	0.48	0.70	0.019	0.027	
D	15.25	15.75	0.60	0.62	
D1	1.27	typ.	0.05 typ.		
E	10	10.40	0.39	0.41	
е	2.40	2.70	0.094	0.106	
e1	4.95	5.15	0.19	0.20	
F	1.23	1.32	0.048	0.052	
H1	6.20	6.60	0.24	0.26	
J1	2.40	2.72	0.094	0.107	
L	13	14	0.51	0.55	
L1	3.50	3.93	0.137	0.154	
L20	16.40 typ.		0.64 typ.		
L30	28.90 typ.		1.13 typ.		
ØP	3.75	3.85	0.147	0.151	
Q	2.65	2.95	0.104	0.116	

Ordering Information FERD60M45C

# **3** Ordering Information

**Table 6. Ordering information** 

Order code	Marking	Package	Weight	Base qty	Delivery mode
FERD60M45CT	FERD60M45CT	TO-220AB	2.2 g	50	Tube

## 4 Revision history

Table 7. Document revision history

Date	Revision	Description of Changes
13-Nov-2013	1	Previous version

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